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CONFIRMATION NO. 6319

SERIAL NUMBER 09/885,553 RULE CLASS 257 RULE ROUP ART UNIT 2826 GR 98 P 1379 D APPLICANTS Lars-Peter Heineck, Paris, FRANCE; Giorgio Schweeger, Draveil, FRANCE; ****CONTINUING DATA***** This application is a DIV of 09/272,968 03/19/1999 PAT 6,281,079 ****FOREIGN APPLICATIONS***** GERMANY 198 12 212.8 03/19/1998 In (DIV) parent file ##* IF REQUIRED, FOREIGN FILING LICENSE GRANTED ****07/18/2001											
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